CD4007UB Types

CMOS
Dual Complementary Pair Plus Inverter

High-Voltage Types (20-Volt Rating)

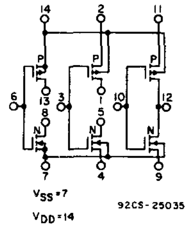
The RCA-CD4007UB types are comprised of three n-channel and three p-channel enhancement-type MOS transistors. The transistor elements are accessible through the package terminals to provide a convenient means for constructing the various typical circuits as shown in Fig. 2.

More complex functions are possible using multiple packages. Numbers shown in parentheses indicate terminals that are connected together to form the various configurations listed.

The CD4007UB types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

Features:

- **Standardized symmetrical output characteristics**
- **Medium Speed Operation – t_{PHL}, t_{PLH} = 30 ns (typ.) at 10 V**
- **100% tested for quiescent current at 20 V**
- **Meets all requirements of JEDEC Tentative Standard No. 13A, "Standard Specifications for Description of 'B' Series CMOS Devices"**
- **Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C**



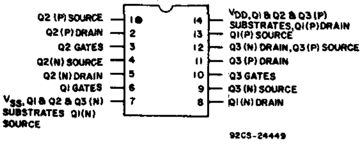
Terminal No.14 – V_{DD}
Terminal No. 7 – V_{SS}

FUNCTIONAL DIAGRAM

Applications:

- **Extremely high-input impedance amplifiers**
- **Shapers**
- **Inverters**
- **Threshold detector**
- **Linear amplifiers**
- **Crystal oscillators**

TERMINAL DIAGRAM
Top View



RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C) Values at –55, +25, +125 Apply to D, F, K, H Packages Values at –40, +25, +85 Apply to E Package							UNITS
	V_O (V)	V_{IN} (V)	V_{DD} (V)					+25			
				–55	–40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	0.25	0.25	7.5	7.5	–	0.01	0.25	μA
	–	0,10	10	0.5	0.5	15	15	–	0.01	0.5	
	–	0,15	15	1	1	30	30	–	0.01	1	
	–	0,20	20	5	5	150	150	–	0.02	5	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3 4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	–0.64	–0.61	–0.42	–0.36	–0.51	–1	–	
	2.5	0,5	5	–2	–1.8	–1.3	–1.15	–1.6	–3.2	–	
	9.5	0,10	10	–1.6	–1.5	–1.1	–0.9	–1.3	–2.6	–	
	13.5	0,15	15	–4.2	–4	–2.8	–2.4	–3.4	–6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	4.5	–	5	1				—	—	1	V
	9	–	10	2				—	—	2	
	13.5	–	15	2.5				—	—	2.5	
Input High Voltage, V_{IH} Min.	0.5	–	5	4				4	—	—	
	1	–	10	8				8	—	—	
	1.5	–	15	12.5				12.5	—	—	
Input Current I_{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) . . . . . . −0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS . . . . . . −0.5 to V_{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT . . . . . . ±10 mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = −40 to +60°C (PACKAGE TYPE E) . . . . . . 500 mW
For T_A = +60 to +85°C (PACKAGE TYPE E) . . . . . . Derate Linearly at 12 mW/°C to 200 mW
For T_A = −55 to +100°C PACKAGE TYPES D, F, K) . . . . . . 500 mW
For T_A = +100 to +125°C (PACKAGE TYPES D, F, K) . . . Derate Linearly at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) . . . . . 100 mW
OPERATING-TEMPERATURE RANGE (T_A):
PACKAGE TYPES D, F, K, H . . . . . . −55 to +125°C
PACKAGE TYPE E . . . . . . −40 to +85°C
STORAGE TEMPERATURE RANGE (T_{stg}) . . . . . . −65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10 s max. . . . . +265°C

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C; *Input t_r, t_f = 20 ns,* C_L = 50 pF, R_L = 200 KΩ

CHARACTERISTIC		CONDITIONS	ALL TYPES LIMITS		UNITS
		V_{DD} Volts	Typ.	Max.	
Propagation Delay Time:	t_{PHL}, t_{PLH}	5	55	110	ns
		10	30	60	
		15	25	50	
Transition Time	t_{THL}, t_{TLH}	5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance	C_{IN}	Any Input	10	15	pF

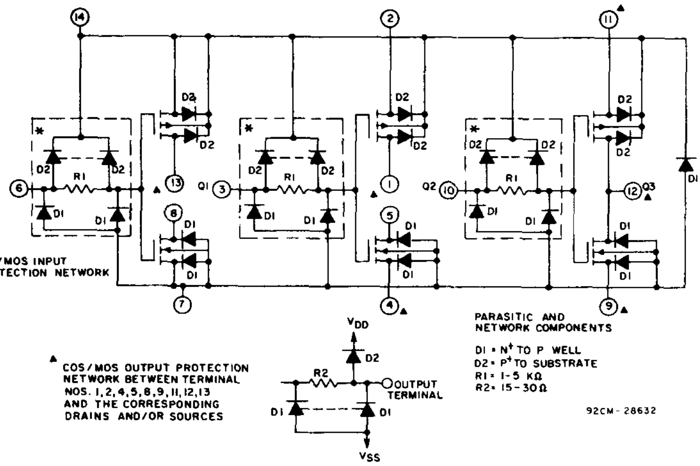
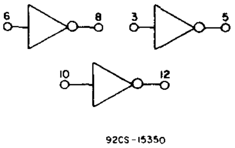


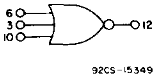
Fig. 1 – Detailed schematic diagram of CD4007UB showing input, output, and parasitic diodes.

a) Triple Inverters



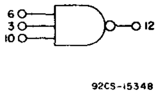
(14,2,11); (8,13);
(1,5); (7,4,9)

b) 3-Input NOR Gate



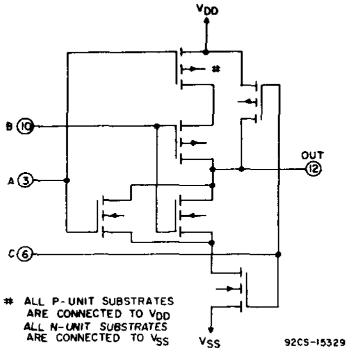
(13,2); (1,11);
(12,5,8); (7,4,9)

c) 3-Input NAND Gate



(1,12,13); (2,14,11);
(4,8); (5,9)

d) Tree (Relay) Logic



(13,12,5); (4,9,8);
(14,2); (1,11)

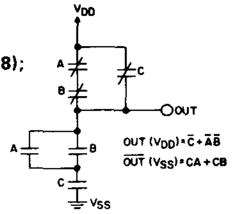
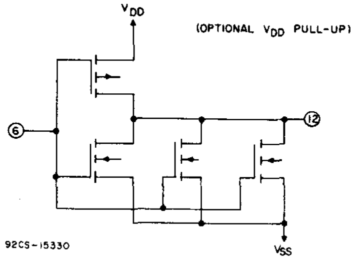


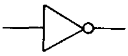
Fig. 2 – Sample COS/MOS logic circuit arrangements using type CD4007UB.

CD4007UB Types

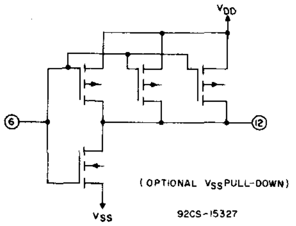
e) High Sink-Current Driver



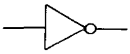
(6,3,10); (8.5, 12); (11,14); 7,4,9)



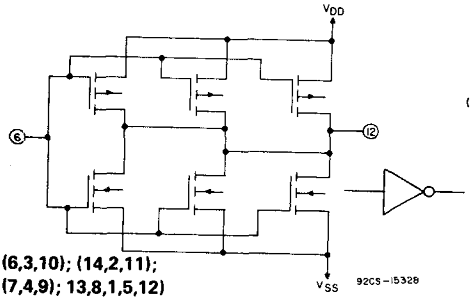
f) High Source-Current Driver



(6,3,10); (13,1,12); (14,2,11); (7,9)

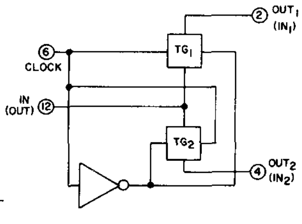


g) High Sink - and Source-Current Driver



(6,3,10); (14,2,11); (7,4,9); 13,8,1,5,12)

h) Dual Bi-Directional Transmission Gating



(1,5,12); (2,9); (11,4); (8,13,10); (6,3)

Fig. 2 – Sample COS/MOS logic circuit arrangements using type CD4007UB (Cont'd).

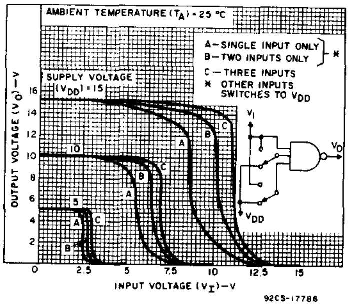


Fig. 3 – Typical voltage-transfer characteristics for NAND gate.

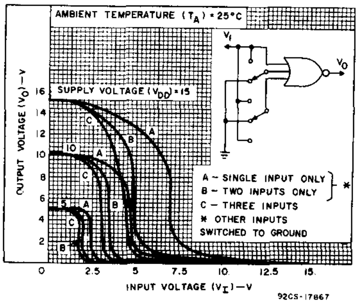


Fig. 4 – Typical voltage-transfer characteristics for NOR gate.

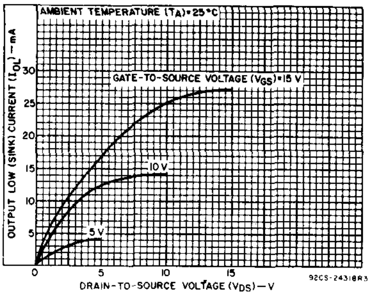


Fig. 5 – Typical output low (sink) current characteristics.

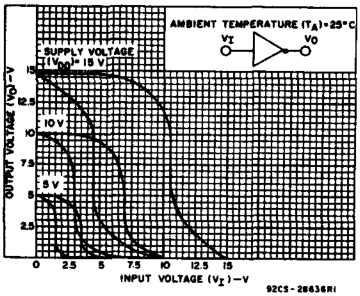


Fig. 6 – Minimum and maximum voltage-transfer characteristics for inverter.

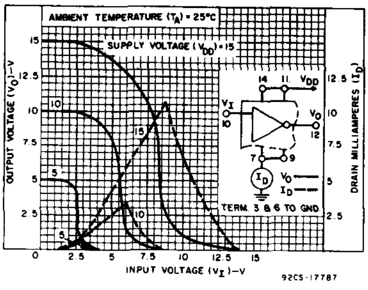


Fig. 7 – Typical current and voltage-transfer characteristics for inverter.

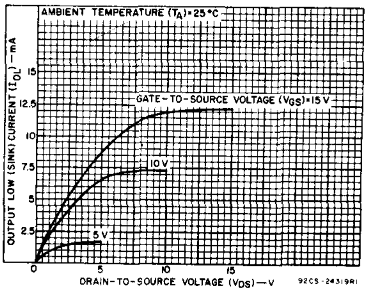


Fig. 8 – Minimum output low (sink) current characteristics.

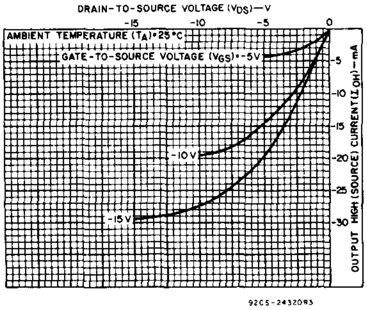


Fig. 9 – Typical output high (source) current characteristics.

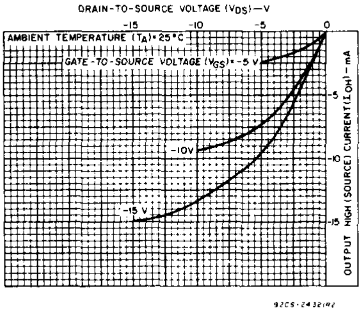


Fig. 10 – Minimum output high (source) current characteristics.

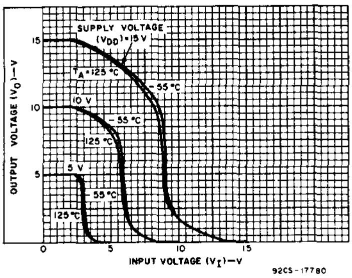


Fig. 11 – Typical voltage-transfer characteristics as a function of temperature.

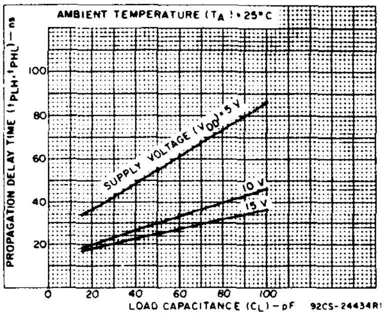


Fig. 12 – Typical propagation delay time vs. load capacitance.

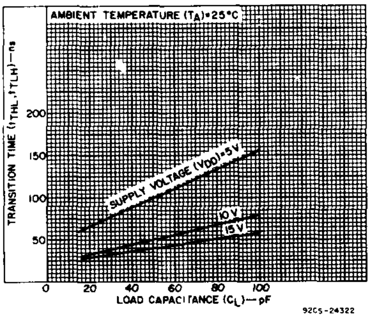


Fig. 13 – Typical transition time vs. load capacitance.

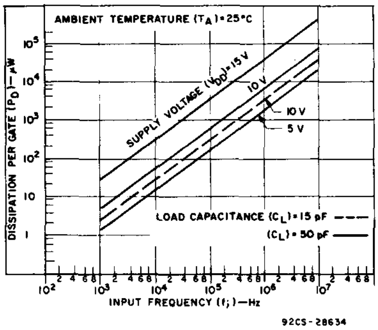


Fig. 14 – Typical dissipation vs. frequency characteristics.

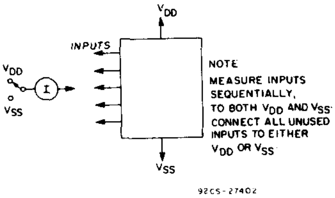


Fig. 15 – Input current test circuit.

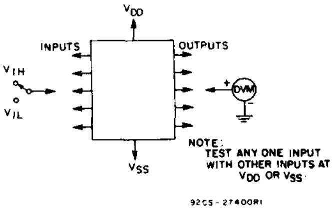


Fig. 16 – Input voltage test circuit.

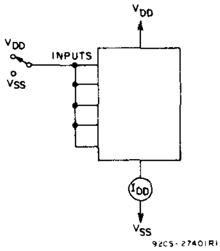
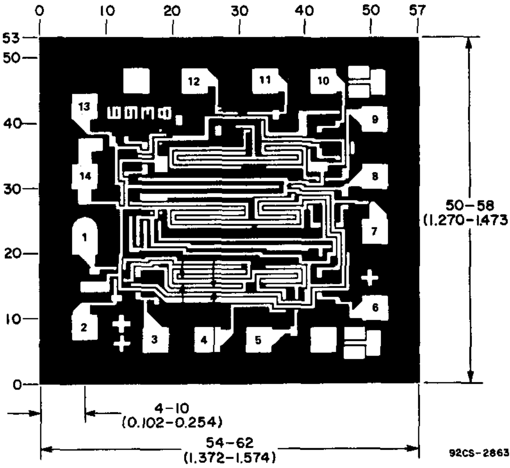


Fig. 17 – Quiescent device current test circuit.



DIMENSIONS AND PAD LAYOUT FOR CD4007UBH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of −3 mils to +16 mils applicable to the nominal dimensions shown.